

2N2904 2N2904A
2N2905 2N2905A

PNP SILICON TRANSISTOR



TO-39 CASE



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N2904, 2N2905 series types are PNP silicon transistors manufactured by the epitaxial planar process, designed for small signal, general purpose and switching applications.

MARKING: FULL PART NUMBER

	SYMBOL	2N2904	2N2904A	UNITS
		2N2905	2N2905A	
Collector-Base Voltage	V_{CBO}	60	60	V
Collector-Emitter Voltage	V_{CEO}	40	60	V
Emitter-Base Voltage	V_{EBO}		5.0	V
Continuous Collector Current	I_C		0.6	A
Power Dissipation	P_D		0.6	W
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D		3.0	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +200		$^\circ\text{C}$

SYMBOL	TEST CONDITIONS	2N2904		2N2904A		UNITS
		2N2905		2N2905A		
		MIN	MAX	MIN	MAX	
I_{CBO}	$V_{CB}=50\text{V}$	-	20	-	10	nA
I_{CEV}	$V_{CE}=30\text{V}, V_{EB}=0.5\text{V}$	-	-	-	50	nA
BV_{CBO}	$I_C=10\mu\text{A}$	60	-	60	-	V
BV_{CEO}	$I_C=10\text{mA}$	40	-	60	-	V
BV_{EBO}	$I_E=10\mu\text{A}$	5.0	-	5.0	-	V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	-	0.4	-	0.4	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$	-	1.6	-	1.6	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	-	1.3	-	1.3	V
$V_{BE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$	-	2.6	-	2.6	V
		2N2904		2N2905		
		2N2904A		2N2905A		
		MIN	MAX	MIN	MAX	
h_{FE}	$V_{CE}=10\text{V}, I_C=100\mu\text{A}$ (2N2904, 2N2905)	20	-	35	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=100\mu\text{A}$ (2N2904A, 2N2905A)	40	-	75	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$ (2N2904, 2N2905)	25	-	50	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$ (2N2904A, 2N2905A)	40	-	100	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=10\text{mA}$ (2N2904, 2N2905)	35	-	75	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=10\text{mA}$ (2N2904A, 2N2905A)	40	-	100	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=150\text{mA}$	40	120	100	300	
h_{FE}	$V_{CE}=10\text{V}, I_C=500\text{mA}$ (2N2904, 2N2905)	20	-	30	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=500\text{mA}$ (2N2904A, 2N2905A)	40	-	50	-	

R1 (11-June 2012)

2N2904 2N2904A
2N2905 2N2905A

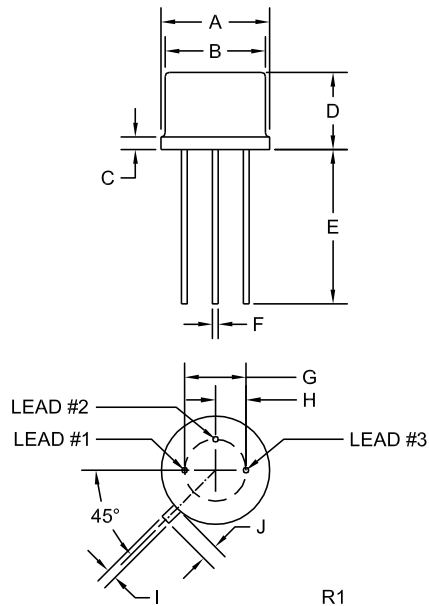
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ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
f_T	$V_{CE}=20\text{V}$, $I_C=50\text{mA}$, $f=100\text{MHz}$	200		MHz
C_{ob}	$V_{CB}=10\text{V}$, $f=100\text{kHz}$		8.0	pF
t_{on}	$V_{CC}=30\text{V}$, $I_C=150\text{mA}$, $I_B=15\text{mA}$		45	ns
t_{off}	$V_{CC}=6.0\text{V}$, $I_C=150\text{mA}$, $I_{B1}=I_{B2}=15\text{mA}$		180	ns

TO-39 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.335	0.370	8.51	9.40
B (DIA)	0.315	0.335	8.00	8.51
C	-	0.040	-	1.02
D	0.240	0.260	6.10	6.60
E	0.500	-	12.70	-
F (DIA)	0.016	0.021	0.41	0.53
G (DIA)	0.200		5.08	
H	0.100		2.54	
I	0.028	0.034	0.71	0.86
J	0.029	0.045	0.74	1.14

TO-39 (REV: R1)

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

MARKING: FULL PART NUMBER

R1 (11-June 2012)